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Single crystal growth of $CeTAl_3$ ($T = Cu, Ag, Au, Pd$ and Pt)

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Abstract

We report single crystal growth of the series of $CeTAl_3$ compounds with $T = Cu, Ag, Au, Pd$ and Pt by means of optical float zoning, where high crystal quality was confirmed in a thorough characterization process. With the exception of $CeAgAl_3$, all compounds crystallize in the non-centrosymmetric tetragonal $BaNiSn_3$ structure (space group: $I4mm$, No. 107), whereas $CeAgAl_3$ adopts the related orthorhombic $PbSbO_2Cl$ structure (Cmcm, No. 63). An attempt to grow $CeNiAl_3$ resulted in the composition $CeNi_2Al_5$. Low temperature resistivity measurements down to ~ 0.1 K did not reveal evidence suggestive of magnetic order in $CePtAl_3$ and $CePdAl_3$. In contrast, $CeAuAl_3$, $CeCuAl_3$ and $CeAgAl_3$ display signatures of magnetic transitions at 1.3 K, 2.1 K and 3.2 K, respectively. This is consistent with previous reports of antiferromagnetic order in $CeAuAl_3$ and $CeCuAl_3$ as well as ferromagnetism in $CeAgAl_3$, respectively.

Keywords: float zone technique, single crystal growth, rare earth compounds, magnetic materials, crystal structure determination, electrical resistivity

1. Introduction

Cerium-based intermetallic compounds represent an ideal testing ground for the study of novel electronic ground states and unusual low-lying excitations, where valence fluctuations, heavy-fermion behaviour, unconventional superconductivity and exotic forms of spin and charge order are ubiquitous. Despite many decades of intense research, the understanding of the nature of strong electronic correlations in Ce-based systems is still rather qualitative. A scenario that is widely alluded to when addressing correlations in f-electron systems considers the competition of Ruderman-Kittel-Kasuya-Yosida (RKKY) interactions, supporting magnetic order, with the single-impurity Kondo effect quenching magnetic moments. While there have been various attempts to advance the understanding, simultaneous treatment of multiple,

nearly equivalent energy scales such as exchange and dipolar interaction, spin-orbit coupling, crystal electric fields and strong magneto-elastic coupling has not been attempted.

Given this general context, the class of $CeTX_3$, where T is a transition metal element and X a simple metal, offer important new insights. For instance, selected members of this series have been discovered, which exhibit a coexistence of magnetic order and superconductivity under pressure. Another line of research pursues the strong coupling of phonons with relatively low lying crystal electric fields (CEF) levels. An important example has been reported in $CeCuAl_3$ [1], which was interpreted in terms of a quasi-bound vibron state first observed in $CeAl_2$ [2, 3]. However, recent studies in $CePd_2Al_2$, as well as preliminary work in other members of the $CeTX_3$ series suggest, that strong interactions of the crystal fields with the spectrum of phonons somewhat akin the claim of vibrons in $CeCuAl_3$, is more generic than assumed so far.

In this paper we report single crystal growth of

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the series $CeTAl_3$ with $T = Cu, Ag, Au, Pd$ and Pt . For our study we have used optical float zoning, to the best of our knowledge, for the first time in the class of $CeTX_3$ systems. This technique has been successfully used in different Ce-based systems, including $CeSi_{2-\sigma}$ [4], $CeCu_2Si_2$ [5] and $CeNi_2Ge_2$ [6]. Following a thorough characterisation, we determined the crystal structure of the systems studied. The high sample quality achieved in our study is corroborated in measurements of the electrical resistivity, which were performed at temperatures down to 0.1 K.

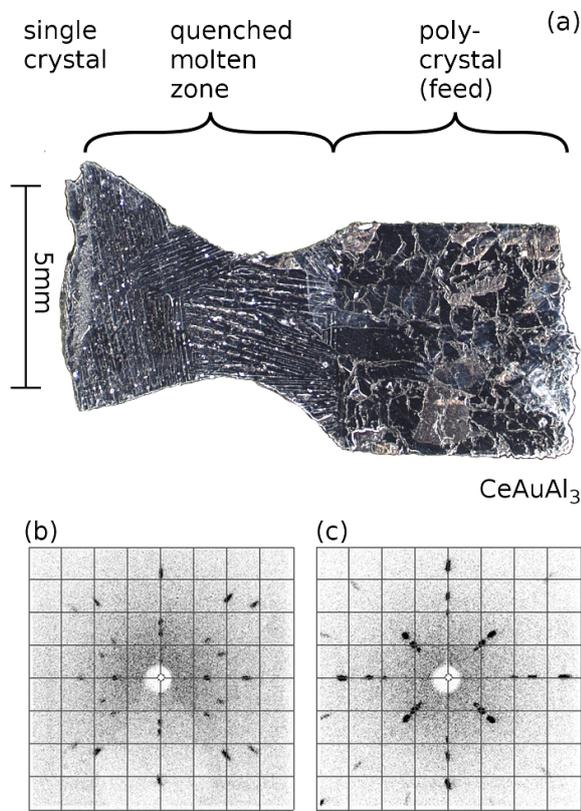


Figure 1: (a) Cut through the quenched final zone of the $CeAuAl_3$ crystal along the rotational symmetry axis. Polycrystalline part of the feed rod, quenched molten zone and beginning of the single crystal are visible. The quenched molten zone features a pronounced stripe pattern. Laue X-ray images along crystallographic a - and c -axes are shown in panels (b) and (c), respectively.

All crystal structures reported in the literature for the series of $CeTAl_3$ compounds are derived from the $BaAl_4$ structure, depicted in Fig. 2(a). The $BaAl_4$ structure is tetragonally body-centred with eight Ce-atoms at the corners and one in the

center. The aluminum atoms are arranged in six planes parallel to ab in the unit cell. The following three important types of structures may be derived from the $BaAl_4$ structure in which the Al and T atoms are ordered.

(i) The $ThCr_2Si_2$ ($I4/mmm$) structure, shown in Fig. 2(b), has so far been most frequently reported for intermetallic compounds. The sequence of layers along the c -direction is given as A-[X-T-X]-A with A a rare-earth metal, T the transition metal element and X either Si, Ge or Al. Typical examples include CeT_2X_2 compounds ($CeCu_2Si_2$ [7], $CeCu_2Ge_2$ [8], $CePd_2Si_2$, $CeRh_2Si_2$ [9]) as well as URu_2Si_2 [10] and $BaFe_2As_2$ [11].

(ii) The $CaBe_2Ge_2$ ($P4/nmm$) variant of the $BaAl_4$ structure, shown in Fig. 2(c), is also characterised by full inversion symmetry and a layered appearance along the c -axis following the sequence A-[X-T-X]-A-[T-X-T]-A. The $CaBe_2Ge_2$ structure has so far been found less frequently because different atom sizes can not be matched as well as for $ThCr_2Si_2$ [12]. An important example for the $CaBe_2Ge_2$ structure of immediate relevance to the Al-based compounds addressed in our study is $CePd_2Al_2$ [13].

(iii) The $BaNiSn_3$ ($I4mm$) structure is the only subtype lacking an inversion center. In recent years Ce-systems with a $BaNiSn_3$ -type structure have generated great interest, since the discovery of superconductivity in heavy fermion systems such as $CeIrSi_3$, $CeRhSi_3$ [14], and $CeCoGe_3$ [15]. In these systems the superconducting pairing symmetry may be outside traditional classification schemes. Shown in Fig. 2(d) is the characteristic unit cell, where the stacking sequence of layers A-T-X(1)-X(2)-A-T-X(1)-X(2)-A may be readily seen. The point group of these systems is C_{4v} , lacking a mirror plane.

In the following, a brief overview over the literature on $CeTAl_3$ compounds is given. Key properties reported are summarised in Table 1. The crystal structure has been determined as $I4mm$ in $CeAuAl_3$ as well as $CeCuAl_3$ in both poly- and single crystals. For $CeAgAl_3$ no distinction has been possible between $I4mm$ and $I4/mmm$, whereas $CePtAl_3$ was reported to adopt a centrosymmetric variant $I4/mmm$. Interestingly, $CePdAl_3$ has so far been reported to crystallize in the orthorhombic $Fmm2$ structure.

Compared to the textbook examples of 3d magnets, crystal electric fields in 4f compounds are weak. Nevertheless, the crystal fields influence the

	Mag	crystal	space group	$T_{C/N}$ (K)	T_K (K)	γ (mJ/molK ²)	μ_{eff} (μ_B)	μ_{CW} (μ_B)
CeCuAl ₃	AFM	pc, sc	$I4mm$ [16, 17, 18]	2.1 [19, 20]	8 [19]	140 [19]	1.8 [17]	2.61 [19]
CeAgAl ₃	FM	pc	$I4/mmm$ or $I4mm$ [21]	3.2 [21]	-	-	-	2.23 [21]
CeAuAl ₃	AFM	pc	$I4mm$ [22, 23, 24]	1.32 [23]	4.5 [23]	227 [23]	2.1 [17]	2.6-2.8 [24]
CePdAl ₃	AFM	pc	$Fmm2$ [25]	6 [25]	-	-	-	-
CePtAl ₃	SG	pc	$I4/mmm$ [17, 26]	0.8 [26, 25]	-	-	1.8 [17]	2.08 [26]

Table 1: Resume of CeTAl₃ properties in literature. AFM - antiferromagnetism, FM - ferromagnetism, SG - Spin-Glass; pc - polycrystal, sc - singlecrystal; $T_{C/N}$ - Curie/Neel-temperature, T_K - Kondo-temperature; μ_{eff} - effective moment, μ_{CW} - Curie-Weiss moment

magnetic properties of 4f systems rather strongly. By Hund's rule, Ce³⁺ has a six-fold degenerate ground state, split into three Kramers doublets by the tetragonal crystal field. In CeCuAl₃ it has been reported that the crystal fields are $\Delta_1=15$ K and $\Delta_2=238$ K [19, 27]. Further for CeAuAl₃ excited levels of $\Delta_1=57$ K and $\Delta_2=265$ K [23] as well as $\Delta_1=60$ K and $\Delta_2=240$ K [24] have been reported.

Magnetic ground states reported for CeTX₃ compounds are typically antiferromagnetic, as in CeCuAl₃ with $T_N=2.1$ K and CeAuAl₃ with $T_N=1.32$ K. However, the exact magnetic ground states reported are incommensurately modulated, with a propagation vector $\mathbf{k}=(0.4, 0.6, 0)$ in the case of CeCuAl₃ [28] and $\mathbf{k}=(0, 0, 0.52)$ for CeAuAl₃ [29]. In contrast, CeAgAl₃ has been reported to represent a rare example of a ferromagnetic Ce-compound with an ordering temperature of $T_C=3.2$ K. Last but not least, CePdAl₃ has been reported to order antiferromagnetically below 6 K, whereas polycrystalline CePtAl₃ has been reported to display spin-glass behaviour below 0.8 K.

All magnetic compounds are characterized by an easy *ab*-plane and a magnetically hard *c*-axes. Kondo temperatures have been determined in CeCuAl₃ at 8 K and in CeAuAl₃ at 4.5 K, where a weak screening of less than 25 % has been found in an ²⁷Al-NMR study [30]. Both compounds show a heavy fermion ground state, as inferred from an electronic contribution to the specific heat of $\gamma=227$ mJ/molK² as well as a large prefactor of quadratic temperature dependence of the electric resistivity of $A=5.0$ $\mu\Omega\text{cm}/\text{K}^2$ in CeAuAl₃ [23] and $\gamma=140$ mJ/molK² in CeCuAl₃. Under pressure, T_N has been reported to rise up to 60 kbar in CeCuAl₃ suddenly vanishing above 80 kbar [31, 32], putatively pointing towards the existence of a quan-

tum critical point (QCP). Further, recently, a phonon - crystal field quasibound state referred to as vibron has been reported in CeCuAl₃ [1], which appears to be absent in CeAuAl₃ [29]. Likewise, an anomalous low energy excitation [33] and phonon scattering by Ce magnetic moment fluctuations have been reported in CeAuAl₃ [34], as well as a possible second phase transition at 0.18 K [29].

2. Experimental Methods

The physical properties of rare earth containing compounds tend to be very sensitive to defects and impurities. In turn, we have made great efforts to reduce the formation of such defects and contamination by impurities to the lowest possible level. Notably, the procedure of the single-crystal preparation is based on the use of high-purity starting elements and a bespoke work-flow that is optimised to minimise contamination by oxygen, nitrogen and hydro-carbons. As the perhaps most important aspect, we have used optical float-zoning (OFZ) representing a crucible-free technique.

Metal lumps of Ce (Ames, 99.9995%), Au and Ag shot (AlfaAesar Premion, 99.995% 99.9999%), copper lumps (MaTecK, 99.9999%), Pd and Pt powder (AlfaAesar Premion, both 99.995%) and Al lump (MaTecK, 99.9999%) were used for the preparation of the feed and seed rods. Ce and Al were weighted in an argon glove box system. First CeAl₂ was prepared in an induction heated horizontal copper cold boat system that can be loaded by means of a bespoke load-lock from a glove box [35]. This reduces contamination of the Ce with oxygen, as the educt CeAl₂ is stable on air. In a second step, the CeAl₂ was then reacted with the transition metals $T = \text{Cu, Ag, Au, Pd}$ or Pt and additional Al in

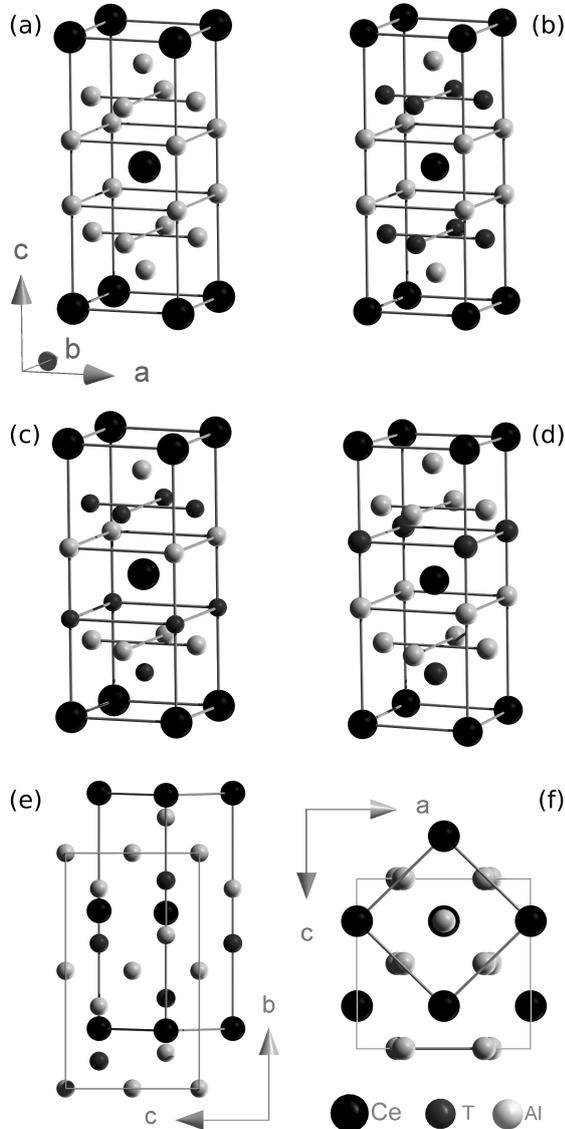


Figure 2: Overview over the BaAl_4 parent structure and important subtypes derived of this structure. (a) BaAl_4 with space group $I4/mmm$ and full inversion symmetry. (b) ThCr_2Si_2 with space group $I4/mmm$ and full inversion symmetry. (c) CaBe_2Ge_2 with space group $P4/nmm$ and full inversion symmetry. (d) BaNiSn_3 with space group $I4mm$, lacking inversion symmetry. (e) and (f) Schematic representation of the BaNiSn_3 structure type and the Cmcm (PbSbO_2Cl) structure type.

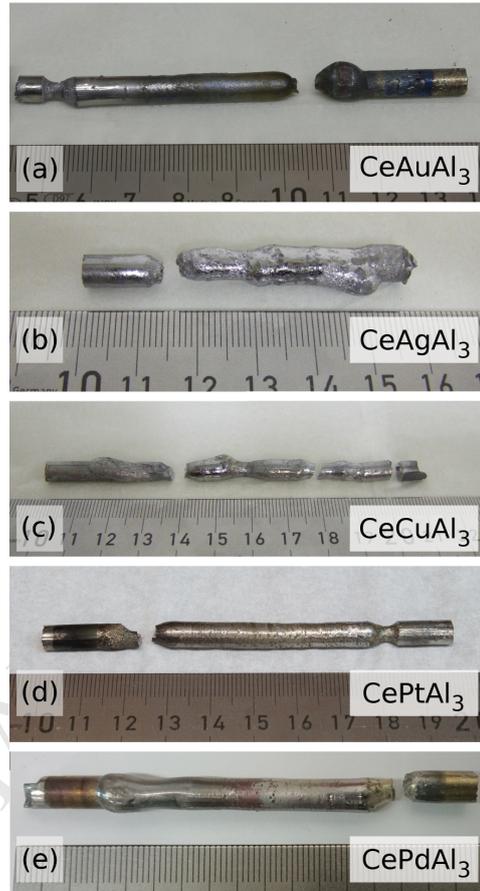


Figure 3: Photographs of all specimen grown by optical float zoning for this study. Scale in cm. (a) CeAuAl_3 (b) CeAgAl_3 (c) CeCuAl_3 (d) CePtAl_3 (e) CePdAl_3

a water cooled Hukin-type radio frequency heated copper crucible.

The polycrystalline samples were remelted and flipped over several times to ensure good homogeneity. The resulting pellets were subsequently cast into cylindrical feed and seed rods with a diameter of 6 mm and a length of 40 to 60 mm's. Furthermore, synthesis of a polycrystalline sample of CeNiAl_3 was attempted by means of our rod casting furnace. For CeAuAl_3 the ternary compound was prepared without the intermediate step of first synthesising CeAl_2 by means of the glove box and the horizontal cold boat system and the bespoke load-lock.

The actual single crystal growth was performed in a CSI 4-mirror (model FZ-T 10000-H-III-VPS) optical float zone furnace. The furnace was re-designed to be all-metal sealed. Prior to growth

the furnace was baked with bespoke heating jackets [36]. 500 W halogen lamps were used for the growth process under a static argon atmosphere at a pressure of 2.5 bar. The float zoning was performed with a growth rate of 5 mm/h and a counter rotation of 6 rpm of the feed and seed rod, respectively.

The characterization of the crystals proceeded as follows. First, all crystals were examined under an optical light microscope. Laue X-ray (Multi-wire Laboratories MWL 110) images were taken on different spots covering all of the surface of the ingot to identify the single crystalline part and possible grain boundaries. In CeAuAl₃ additionally cross sections of the upper and lower part of the crystal were analysed as well as a cut through the quenched final part of the molten zone. Figure 1 (a) shows from right to left the polycrystalline feed rod, the quenched molten zone with a pronounced stripe structure and the beginning of the single crystal at the lower end.

All crystals were oriented by Laue X-ray diffraction. Fig. 1(b) and (c) show typical Laue pictures of CeAuAl₃ for the *a*- and *c*-axes, respectively. The composition was confirmed by single crystal and powder X-ray diffraction. For CeAuAl₃ additional scanning electron microscope images and energy dispersive X-ray spectra were recorded.

Small single crystals with dimensions less than 100 μm were mechanically extracted from CeTAl₃ ($T = \text{Cu, Ag, Au, Pd}$ and Pt) ingots as grown. Generally all tested crystals were of high quality with sharp diffraction peaks. Intensity data were collected with graphite-monochromatized Mo K α X-ray radiation. Three-dimensional data were indexed, integrated and corrected for Lorentz-, polarization, absorption and background effects using a diffractometer specific software, namely CrystalClear for a Rigaku Saturn724+ and X-Area for a STOE IPDS II. Initial structure analysis/solution (using direct methods) for CeTAl₃ ($T = \text{Cu, Ag, Au, Pt}$) was done with SHELX-2012 as implemented in the program suite WinGX 2014.1 [37]. The crystal structure of modulated CePdAl₃ was solved using WinCSD [38]. The experimental data and results of the structure refinement for selected samples are reported in Table 3, while the fractional atomic coordinates, occupation numbers and equivalent isotropic, and anisotropic atomic displacement parameters are listed in Table 4 and 5.

Samples for resistivity measurements were cut from the single-crystalline sections of the ingots with a diamond wire saw. Typical dimension of

the samples were between 4 and 6 \times 1 \times 0.2 mm³, oriented such that the electrical current could be applied along longest direction which corresponding to the *c*-axis. The resistivity was measured in a standard four-probe ac-configuration using a digital lock-in amplifier and an excitation current of 5 mA at an excitation frequency of 22.08 Hz. Room temperature transformers were used for impedance matching. Data were recorded between 2 K and 300 K in a standard ⁴He cryostat. Data down to much lower temperatures were measured for CeTAl₃ with $T = \text{Cu, Ag, Au}$ in an adiabatic demagnetisation refrigerator (ADR) using the same detection technique at a lower excitation current of 1 mA down to a temperature below \sim 300 mK. For samples with $T = \text{Pt, Pd}$ a ³He/⁴He dilution refrigerator was used down to temperatures well below 100 mK.

3. Experimental Results

3.1. Crystal Structure

The actual growth process resulted in the specimens shown in Fig. 3. We obtained large single crystals of CeAuAl₃, CeCuAl₃ and CePtAl₃ shown in Figs. 3 (a), (c) and (d), respectively. While these ingots remained mechanically intact after growth, the CeCuAl₃ ingot (shown in Fig. 3 (a)) fractured spontaneously in one location after cool-down. For CeAgAl₃ single crystalline grains were prepared from the specimen. The molten zone in the growth process of CePdAl₃ was very unstable and we could only prepare small single crystalline samples with a typical size of up to 3 mm. A second attempt to grow CePdAl₃ with a reduced growth rate of 1 mm/h allowed to obtain the large single crystal depicted in Fig. 3 (e). Note that all measurements on CePdAl₃ reported in this paper were carried out on samples cut from the first crystal.

Additionally a weighted-in quantity of CeNiAl₃ was synthesized in the Hukin-type cold crucible. The resulting pellet was analysed by powder X-ray diffraction and revealed a composition CeNi₂Al₅ with CeAl₂ and CeNi₂Al₃, where small single crystals were extracted.

The analysis of the arrays of the diffraction data revealed that the majority of the CeTAl₃ compounds ($T = \text{Cu, Au, Pt}$) studied display reflections consistent with the tetragonal lattice and in line with one of the distorted BaAl₄ structure types. The T/Al antisite disorder essentially corresponds to the local differences between ThCr₂Si₂,

CaBe_2Ge_2 , HoCuAl_3 or BaNiSn_3 structures. Extinction of characteristic reflections revealed a body centred tetragonal lattice and the structure solution corresponded to a BaNiSn_3 type structure for CeAuAl_3 , CeCuAl_3 and CePtAl_3 . The evidence for putative Au/Al antisite disorder in CeAuAl_3 was below the detection limit, whereas for CeCuAl_3 a small Cu/Al mixing on the copper site was observed consistent with a $\sim 5\%$ site occupation factor (sof) deficiency on the $4b$ Al site. A higher degree of antisite disorder was found in the CePtAl_3 sample. Assuming a stoichiometric composition and fully occupied atomic sites of CePtAl_3 , the antisite Pt/Al disorder appeared to be as high as 18% sof at both T and Al $2a$ sites. The obtained unit cell volumes were found to decrease in the series Au – Pt – Cu in accordance with the metallic radii ($r_{\text{Au}} = 1.44 \text{ \AA}$, $r_{\text{Pt}} = 1.39 \text{ \AA}$, $r_{\text{Cu}} = 1.28 \text{ \AA}$) [39].

For CeAgAl_3 a small orthorhombic distortion of the BaAl_4 type lattice of the order of $\sim 0.1 \text{ \AA}$ was detected. The character of the splitting of the reflection and the extinction revealed a C -base centred orthorhombic lattice with $a_0 \approx a_T\sqrt{2}$, $b_0 \approx c_T$ and $c_0 \approx a_T\sqrt{2}$, where O and T denote orthorhombic and tetragonal lattice dimensions. The structure solution leads to the $Cmcm$ space group and a model consistent with the structure type of PbSbO_2Cl . The orthorhombic superstructure observed occurs in oxyhalides and is found rarely in intermetallics, e.g., in LaZn_4 [40] and SrPdGa_3 [41, 42]. Similar to CeCuAl_3 a small Ag/Al mixing occurs on the Ag site along with a weak (ca. 4% sof) deficiency on the $8e$ Al site.

A comparison of the Ag and Au based CeTAl_3 structures is plotted in Fig. 2 (e) and (f). We note, that Ag and Au nominally possess the same metallic radii ($r_{\text{Ag}} = 1.44 \text{ \AA}$), which may correspond to a similar magnitude of chemical pressure in both CeTAl_3 ($T = \text{Ag, Au}$). Indeed, the normalised lattice dimensions of CeAgAl_3 ($a_T \approx (a_0 + b_0)/2\sqrt{2} \approx 4.3566(8) \text{ \AA}$, $c_T \approx 10.837(2) \text{ \AA}$) are very similar to these of CeAuAl_3 . Further, the relative cerium and aluminium positions reproduce well, whereas major differences were noticed for the distribution of gold and silver sites. By their arrangement the structure may be viewed as an intermediate step between BaAl_4 (or HoCuAl_3) and the BaNiSn_3 structure type. The antisite disorder observed smears out the layered structure along the c -axis in CeAgAl_3 , which initially can be described as A - [TX-X-TX] A, where TX indicated mixed T and X layer occupation.

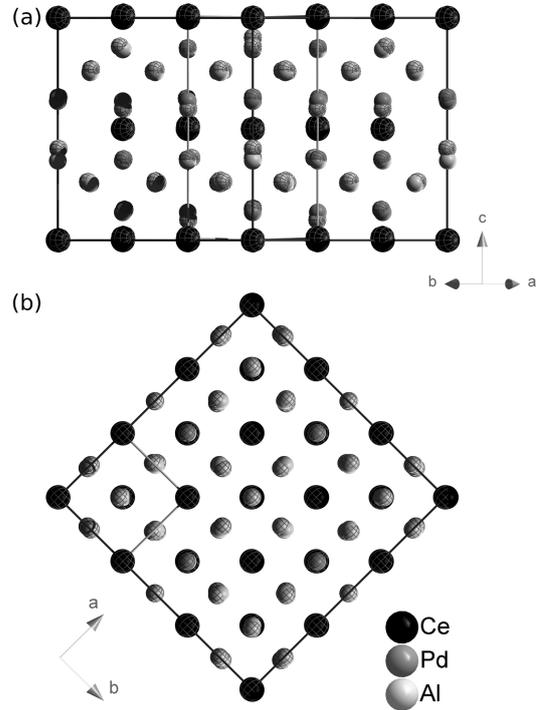


Figure 4: Refined structural modifications of CePdAl_3 : plane atoms - BaNiSn_3 type of structure, structured atoms - *klassengleiche* [43] subgroup of BaNiSn_3 type of structure with $3a$ multiplied axis.

This brings us to CePdAl_3 for which the full structure determination was performed on a small single crystal. The set of Bragg reflections collected for the CePdAl_3 single crystal could neither be described with a conventional tetragonal nor with orthorhombic lattices. Careful indexing was finally found to be consistent with a tetragonal cell with a c -parameter comparable to CeTAl_3 ($T = \text{Cu, Ag, Au, Pt}$), however, with an a lattice parameter multiplied by a factor of ~ 3 . Analysis of peak systematics resulted in a solution corresponding to a body centred tetragonal lattice. This is in agreement with group theory, as the $3a, c$ axis multiplication in the $I4mm$ space group is allowed in the frame of *klassengleiche* [43] subgroups IIc for $I4mm$ ($3a$ structure). Multiplication of the axis implies a splitting of the Ce and Pd positions into three independent sites, whilst the two initial aluminium sites are split into seven positions in the larger cell. Similar to CeCuAl_3 , CePtAl_3 , CeAgAl_3 Rietveld refinement revealed Pd/Al antisite disorder, where,

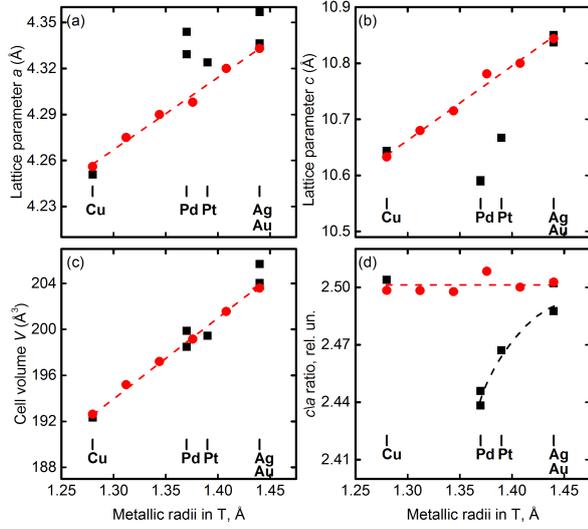


Figure 5: Lattice parameter, cell volume and c/a ratio for different $CeTAl_3$ ($T = Cu, Ag, Au, Pd, Pt$) plotted as a function of T metallic radius (black squares). Data showed by red circles correspond to $CeAu_{1-x}Cu_xAl_3$ solid solution taken from [44]. Two data points for $CePdAl_3$ correspond to $BaNiSn_3$ and $3a$ structures. The lines are showed as guides for the eyes.

however, only one Pd site of three as well as two of the seven Al sites are affected. It is important to emphasize, that the $3a$ structure was only observed in a small $CePdAl_3$ single crystal, and has so far not been confirmed in powder diffraction as explained in the following.

Examination of a crushed and pulverized ingot using lab X-ray powder diffraction did not reveal any hints for a $3a$ structure, but a conventional $BaNiSn_3$ modification for $CePdAl_3$ (see Table 5). The crystal structures of both the $BaNiSn_3$ -type and the $3a$, c axis multiplied modifications of the $CePdAl_3$ structures are shown in Fig. 4. The $Ce(0,0,0)$ atomic position is here used as a reference. In comparison to the $BaNiSn_3$ -type modification of $CePdAl_3$, the $3a$ structure contains a certain degree of Pd/Al disorder and by its layer structure $A - [TX-X-TX] - A$ it becomes very similar to $CeAgAl_3$. An attempt to refine the structure modulation in $CePdAl_3$ was performed assuming both commensurate and incommensurate modulation vectors of the $BaNiSn_3$ parent structure. The atomic modulated displacements were comparable to standard uncertainties of atom localization and improvement to fit residuals (when compared to the structure model with $3a$, c axis multiplication), and

	ρ_0 ($\mu\Omega\text{cm}$)	RRR	$\rho_{300\text{K}}$ ($\mu\Omega\text{cm}$)
$CeCuAl_3$	12.9	2.84	36.6
$CeAgAl_3$	7.9	3.81	30.1
$CeAuAl_3$	15.2	2.50	37.8
$CePdAl_3$	25.1	1.39	35.0
$CePtAl_3$	67.4	1.25	84.1

Table 2: Parameters derived from resistivity measurements on $CeTAl_3$ with $T = Cu, Ag, Au, Pd$ and Pt . ρ_0 is the residual resistivity extrapolated to $T = 0$, RRR the residual resistivity ratio $\rho(300\text{K})/\rho_0$, where $\rho(300\text{K})$ denotes the resistivity at room temperature.

thus, found to be marginal. Taken together this provides strong putative evidence of a $3a$ structure, requiring further studies to be confirmed.

The lattice parameters of the $CeTAl_3$ ($T = Cu, Ag, Au, Pd, Pt$) samples studied were found to be in a good agreement with experimental data reported in Refs. [44, 16, 45, 27, 20]. Cell volumes in $CeTAl_3$ ($T = Cu, Ag, Au, Pd, Pt$) follow a linear dependence as a function of T ionic radii (see Fig. 5) in line with values reported for the $CeAuAl_3$ to $CeCuAl_3$ pseudobinary system [44], which displays a behaviour characteristic of Vegard's law. The observed linear dependence may be viewed in terms of structural changes in $CeTAl_3$ ($T = Cu, Ag, Au, Pd, Pt$) driven by chemical pressure. However, all $CeTAl_3$ studied are characterised by a large anisotropy. Notably, for $CeCuAl_3$, $CeAuAl_3$ and related solid solutions [44] the c/a ratio is nearly constant with $c/a \sim 2.5$. $CePdAl_3$, $CePtAl_3$ and $CeAgAl_3$, display systematically lower c/a values.

For these compounds the experimentally determined a lattice parameters are systematically higher, as well as the c lattice parameters, which are systematically smaller than those observed in the $CeAuAl_3 - CeCuAl_3$ pseudobinary series. Taking into account nominally equal metallic radii for Au and Ag, the differences observed for the a lattice dimensions and cell volume of $CeAuAl_3$ and $CeAgAl_3$ as well as their different structure, significantly reduces the relevance of an approximation in the spirit in terms of chemical pressure and shows that the chemical nature of T in $CeTAl_3$ plays a dominant role for the structure and its distortion.

3.2. Electrical Resistivity

Shown in Fig. 6 (a1) to (a5) is the electric resistivity for $CeTAl_3$ with $T = Cu, Ag, Au, Pd$ and Pt covering three decades of temperature from $\sim 0.1\text{K}$ to 300K . For these data the electrical currents were

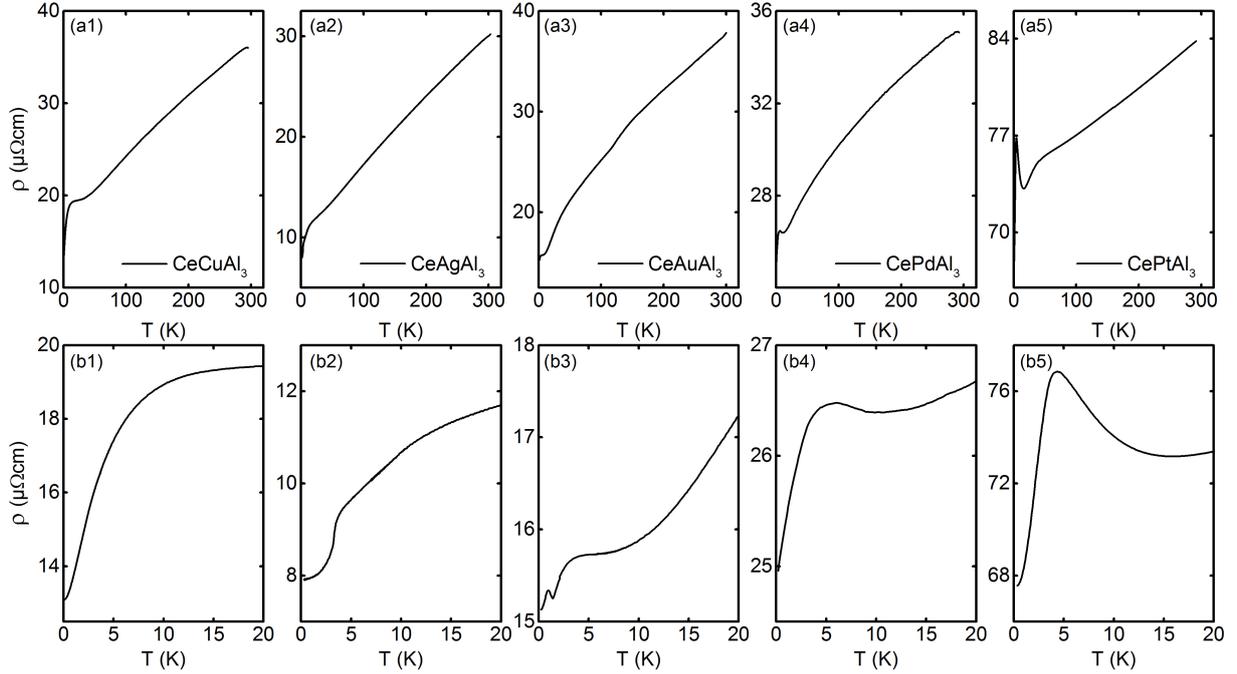


Figure 6: Electrical resistivity for CeTAl_3 with $T = \text{Cu, Ag, Au, Pd, Pt}$. (a1) - (a5) On a large temperature range from $T_{\text{min}} = 300 \text{ mK}$ to 300 K all samples show metallic behaviour. (b1) - (b2). Close-up view of the behaviour at low temperatures up to 20 K .

applied parallel to the crystallographic c -axis. Further, Fig. 6 (b1) - (b5) shows the same data on a temperature scale up to 20 K for a better visibility of the low temperature features.

All samples show metallic behaviour over the complete temperature range. The residual resistivity, resistivity at 300 K and associated residual resistivity ratios (RRR) of all compounds are summarized in Table 2. The residual resistivity ρ_0 for all compounds are among the best reported in literature. The values of the RRR observed are lower than for Si or Ge based compounds, probably due to the remaining antisite disorder in our samples. We wish to note that preliminary work suggests, that careful annealing studies and tiny adjustments to the starting compositions as well as variations of the parameters used for single crystal growth promise considerable improvements as compared to the values observed here.

The key features observed in the temperature dependences may be summarised as follows. In CeCuAl₃ the linear decrease at high temperatures is followed by a plateau between 30 K and 10 K , whereas a clear maximum as reported in Refs. [20,

28] is not observed. The strong decrease below 10 K traditionally is attributed to the coherence of a Kondo lattice, where a clear signature of the magnetic ordering transition at 2.1 K is not observed and maybe hidden by this Kondo coherence. However, on a speculative note an alternative scenario may be related to the strong electron-phonon interactions associated with the quasi-bound vibron. Below 0.5 K the decrease flattens towards a residual resistivity of $12.9 \mu\Omega\text{cm}$, which is among the lowest reported in the literature for this compound.

A linear decrease is observed in CeAgAl₃ down to approximately 17 K , followed by a steeper linear decrease. The change of slope is of unknown origin, but may be due to the changes of the coupling with the lattice degrees of freedom. Such a strong coupling of a crystal electric field (CEF) with a phonon is discussed in CeCuAl₃ [1] and CePd₂Al₂ [46]. A clear kink at 3.2 K , corresponding to the magnetic transition temperature of ferromagnetic order reported in the literature, is followed by a quadratic temperature dependence down to the lowest temperatures. The specific temperature dependence may be characteristic of weakly spin-

polarised Fermi liquid, in which electron magnon scattering is weak.

For CeAuAl₃ the resistivity decreases from 300 K to 15 K in a quasi-linear manner, probably due to crystal electric field effects as discussed in Ref. [23]. With decreasing temperature the decrease of the resistivity is followed by a plateau around 8 K and another strong decrease below the onset of magnetic order at 1.32 K. However the onset of the decrease at 4.5 K is considerably higher than T_c and maybe attributed to the coherence of a Kondo lattice. At ~ 1 K, an additional maximum due to the opening of a super-zone gap is observed reminiscent of behaviour observed in CeGe [47] and Cr [48].

CePdAl₃ shows a sublinear decrease over the entire temperature range, probably due to crystal field effects. A faint maximum is visible around 5.7 K, again attributed to the onset of the Kondo effect, and followed by a strong decrease down to the lowest temperatures, most probably caused by Kondo coherence. Towards the lowest temperatures there is a linear decrease of the resistivity instead of a flattening out. We do not observe any features suggesting magnetic order over the whole temperature range, suggested to exist below 6 K in the literature.

Last but not least, the linear decrease of the resistivity in CePtAl₃ down to ~ 50 K is followed by a stronger decrease to a minimum at 15.9 K. The origin of this kink may be again, as speculated above, related to changes of the coupling to the crystal lattice. An exponential increase to a maximum at 4.3 K is most probably due the onset of Kondo scattering and followed by a strong decrease consistent with Kondo coherence. Towards the lowest temperatures, the decrease flattens and is extrapolated to a residual resistivity of $25.1 \mu\Omega\text{cm}$. Overall, the resistivity is about a factor of three higher than for other compounds studied, which may be due to the higher degree of antisite disorder. There are no signs suggesting magnetic order, however below ~ 0.8 K the decrease of the resistivity flattens out.

4. Conclusions

Single crystals of the non-centrosymmetric intermetallic compounds CeTAl₃ ($T = \text{Cu, Ag, Au, Pd and Pt}$) were grown by means of optical float-zoning, to the best of our knowledge for the first time. Large single crystals were obtained for all compounds except CeAgAl₃. For CePdAl₃ the growth rate had to be reduced from 5 mm/h to

1 mm/h to be stable. An attempt to grow a polycrystal of CeNiAl₃ resulted in a mixture dominated by CeNi₂Al₅. The crystal structure of the parent compounds was determined by single crystal X-ray diffraction. The crystal structure was found to be BaNiSn₃-type $I4mm$ in all cases except for CeAgAl₃, which shows a small distortion corresponding to the orthorhombic $Cmcm$ structure. Further, we find strong putative evidence that the space group of CePdAl₃ has a three fold multiplied lattice parameter a , which is allowed by group theory. Although the unit cell volume for all systems follows the metallic radii of the transition metal element rather well, the c/a ratio is deviating strongly.

Site-antisite disorder of the T and X -site appears to be nominally absent in CeAuAl₃, but reaches a value as high as 18% in CePtAl₃, nominally explaining the larger residual resistivities as compared to the Si and Ge based compounds in this series. While the sample quality of our samples as grown is already high, we expect that careful studies addressing the precise growth conditions and the role of post-growth treatment, such as annealing and/or electro-transport, promise significant improvements.

Further, resistivity measurements as described in the traditional language used for Ce-based compounds are consistent with Kondo behaviour for all samples except CeAgAl₃. The occurrence of the Kondo maximum depends thereby on the transition metal element and is most pronounced for $T = \text{Pt}$. It is interesting to speculate, if, what seems to be Kondo-like behaviour, eventually turns out to be due to strong electron-phonon coupling as related to the notion of the quasi-bound vibron state reported in CeCuAl₃. As a final point, features in the resistivity of CeAuAl₃, CeCuAl₃ and CeAgAl₃ at low temperatures are consistent with published reports of antiferromagnetic order in the former two compounds and ferromagnetism in the latter system, respectively. This contrasts the literature on CePtAl₃ and CePdAl₃, where we do not find signs of magnetic order down to 0.1 K in the resistivity, whereas spin glass order has been reported for polycrystalline CePtAl₃ and antiferromagnetic order for CePdAl₃.

Taken together all single-crystals are of high quality consistent with very low residual resistivities as compared to the literature. This demonstrates that optical float-zoning as employed under pure conditions provides an excellent method for the preparation of Ce-based intermetallic compounds.

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	CeAgAl ₃	CeAuAl ₃	CeCuAl ₃	CePdAl ₃	CePtAl ₃
Diffractometer	Stoe IPDS-II	Rigaku Saturn724+	Stoe IPDS-II	Stoe IPDS-II	Rigaku Saturn724+
Radiation		MoK α			
Wavelength (\AA)		0.71073			
Abs. correction type		empirical			
Abs. coeff. μ	15.737	237.31	16.792	161.11	232.91
Crystal system	Orthorhombic	Tetragonal	Tetragonal	Tetragonal	Tetragonal
space group	Cmcm	I4mm	I4mm	I4mm	I4mm
a (\AA)	6.205(1)	4.3364(4)	4.2508(4)	12.988(1)	4.3239(4)
b (\AA)	10.837(2)	4.3364(4)	4.2508(4)	12.988(1)	4.3239(4)
c (\AA)	6.118(1)	10.850(2)	10.644(1)	10.589(1)	10.667(2)
V (\AA^3)	411.4(1)	204.03(4)	192.32(3)	1786.2(5)	199.43(4)
Z	4	2	2		2
ρ_{calc} (g/cm^3)	5.206	6.805	4.758	5.421	6.930
index range h	-9...9	-5...6	-5...5	-17...17	-6...3
	-16...16	-3...6	-5...5	-17...17	-6...5
	-9...8	-16...14	-14...14	-14...14	-16...16
reflections collected	14323	1821	2475	6685	879
independent reflections	417	226	100	703	141
R _{int} (%)	9.52	3.52	10.49	2.00	3.45
RF2 (%)	6.61	5.25	2.18	8.21	7.60
RF2w (%)	5.45	9.36	5.79	6.29	8.50
RF (%)	3.30	3.78	2.00	5.84	4.81
χ^2	0.369	1.98	1.373	5.84	2.24
no. of free parameters	19	14	14	26	14

Table 3: Experimental details and results of the structure refinement of CeTAl₃ ($T = \text{Cu, Ag, Au, Pd, Pt}$) as studied at ambient conditions.

Atom	Wyckoff	x/a	y/b	z/c	sof	u _{eq}	u ₁₁	u ₂₂	u ₃₃	u ₁₂	u ₁₃	u ₂₃
CeAgAl ₃ , space group <i>Cmcm</i> , a = 6.2050(12) Å, b = 10.837(2) Å, c = 6.118(1) Å												
Ce	4c	0	0.24552(6)	1/4	1.0	0.0105(4)	0.0097(3)	0.0102(3)	0.0117(5)	0	0	0
Ag1	4c	1/2	0.38336(9)	1/4	0.918(8)	0.0133(5)	0.0125(4)	0.0123(5)	0.0150(6)	0	0	0
Al1	4c	1/2	0.38336(9)	1/4	0.082(8)	0.0133(5)	0.0125(4)	0.0123(5)	0.0150(6)	0	0	0
Al2	4c	1/2	0.1512(4)	1/4	1.0	0.013(2)	0.013(17)	0.015(2)	0.011(2)	0	0	0
Al3	8e	0.2309(4)	1/2	0	0.96(1)	0.014(1)	0.014(10)	0.013(1)	0.015(2)	0	0	0.00(1)
CeAuAl ₃ , space group <i>I4mm</i> , a = 4.3364(4) Å, c = 10.850(2) Å												
Ce1	2a	0	0	0	1.0	0.0078(7)	0.0068(6)	0.0068(6)	0.0099(7)	0	0	0
Au1	2a	0	0	0.6356(2)	1.0	0.0124(6)	0.0137(6)	0.0137(6)	0.0099(5)	0	0	0
Al1	2a	0	0	0.406(1)	1.0	0.008(3)	0.003(2)	0.003(2)	0.017(4)	0	0	0
Al2	4b	0	1/2	0.2608(7)	1.0	0.009(3)	0.005(3)	0.011(3)	0.012(3)	0	0	0
CeCuAl ₃ , space group <i>I4mm</i> , a = 4.2508(4) Å, c = 10.644(1) Å												
Ce1	2a	0	0	0	1.0	0.0063(4)	0.0058(4)	0.0058(4)	0.0071(5)	0.000	0.000	0.000
Cu1	2a	0	0	0.6314(3)	0.84(4)	0.008(1)	0.009(1)	0.009(1)	0.008(2)	0.000	0.000	0.000
Al1	2a	0	0	0.6314(3)	0.16(4)	0.008(1)	0.009(1)	0.009(1)	0.008(2)	0.000	0.000	0.000
Al2	2a	0	0	0.4040(8)	1.0	0.009(1)	0.006(2)	0.006(2)	0.015(3)	0.000	0.000	0.000
Al3	4b	0	1/2	0.2489(6)	0.94(4)	0.008(1)	0.008(3)	0.009(3)	0.008(1)	0.000	0.000	0.000
CePtAl ₃ , space group <i>I4mm</i> , a = 4.3239(4) Å, c = 10.667(2) Å												
Ce1	2a	0	0	0	1.0	0.009(1)	0.008(1)	0.008(1)	0.009(2)	0.00000	0.00000	0.00000
Pt1	2a	0	0	0.6364(3)	0.82(1)	0.011(1)	0.013(1)	0.013(1)	0.007(1)	0.00000	0.00000	0.00000
Al1	2a	0	0	0.6364(3)	0.18(1)	0.011(1)	0.013(1)	0.013(1)	0.007(1)	0.00000	0.00000	0.00000
Pt2	2a	0	0	0.386(1)	0.82(1)	0.034(5)	0.021(3)	0.021(3)	0.060(8)	0.00000	0.00000	0.00000
Al2	2a	0	0	0.386(1)	0.18(1)	0.034(5)	0.021(3)	0.021(3)	0.060(8)	0.00000	0.00000	0.00000
Al3	4b	0	1/2	0.257(1)	1.0	0.011(5)	0.010(5)	0.013(5)	0.011(4)	0.00000	0.00000	0.00000

Table 4: Refined fractional atomic coordinates, site occupations as well as equivalent and anisotropic thermal displacement parameters for CeAgAl₃, CeAuAl₃, CeCuAl₃ and CePtAl₃.

Atom	Wyckoff	x/a	y/b	z/c	sof	u_{eq}
(3a) CePdAl ₃ , space group $I4mm$, a = 12.988(1) Å, c = 10.589(1) Å						
Ce1	2a	0	0	0	1.0	0.013(2)
Ce2	8d	0.3333(4)	0	0.0189(9)	1.0	0.009(1)
Ce3	8c	0.3291(4)	0.32918	0.012(2)	1.0	0.013(1)
Pd1	2a	0	0	0.649(2)	1.0	0.009(1)
Pd2	8d	0.5	0.1653(5)	0.875(2)	1.0	0.014(3)
Pd3	8c	0.1696(5)	0.16963	0.155(2)	0.65(2)	0.010(3)
Al1	8c	0.1696(5)	0.16963	0.155(2)	0.34(2)	0.010(3)
Al2	2a	0	0	0.422(3)	0.78(7)	0.010(3)
Pd4	2a	0	0	0.422(3)	0.21(7)	0.010(3)
Al3	4b	0.5	0	0.262(6)	1.0	0.008(9)
Al4	8d	0.5	0.1687(9)	0.102(2)	0.80(3)	0.019(6)
Pd5	8d	0.5	0.1687(9)	0.102(2)	0.19(3)	0.019(6)
Al5	8d	0.5	0.339(3)	0.257(5)	1.0	0.009(8)
Al6	8d	0.159(3)	0	0.271(5)	1.0	0.015(9)
Al7	8c	0.154(2)	0.15476	0.882(4)	1.0	0.024(6)
Al8	16e	0.347(2)	0.168(2)	0.260(3)	1.0	0.008(5)
(BaNiSn ₃) CePdAl ₃ *, space group $I4mm$, a = 4.34396(6) Å, c = 10.5915(2) Å						
Ce1	2a	0	0	0	1.0	0.0316(8)
Pd1	2a	0	0	0.6247(4)	1.0	0.0410(1)
Al1	2a	0	0	0.349(1)	1.0	0.011(1)
Al2	4b	0	1/2	0.2579(8)	1.0	0.011(1)

Table 5: Refined fractional atomic coordinates, site occupations as well as isotropic thermal displacement parameters for two modifications of CePdAl₃. *results were obtained by the evaluation of X-ray powder diffraction data

Highlights for “Single crystal growth of $CeTAl_3$ ($T = Cu, Ag, Au, Pd$ and Pt)

- Single crystal growth in float zone technique of $CeTAl_3$ ($T = Cu, Ag, Au, Pd$ and Pt).
- Crystal structure is $I4mm$ for $T = Au, Cu, Pt, Pd$.
- $CePdAl_3$ shows a three-fold multiplied parameter a .
- Orthorhombic distortion to $Cmcm$ structure is found for $T=Ag$.
- No magnetic order is found for $T = Pt, Pd$ down to 100mK.